

## ABSTRACT OF THE DISCLOSURE

### METHODS FOR MAKING SILICON CONTAINING FILMS THAT HAVE HIGH CARBON CONTENT

- 5 A composition and method for using the composition in the fabrication of an electronic device are disclosed. Compounds, compositions and methods for depositing a low dielectric constant ( $<5.0$ ) and high oxygen ash resistance silicon-containing film such as, without limitation, a carbon doped silicon oxide, are disclosed.

[No figure]